



JX020 Series Sensitive gate SCRs

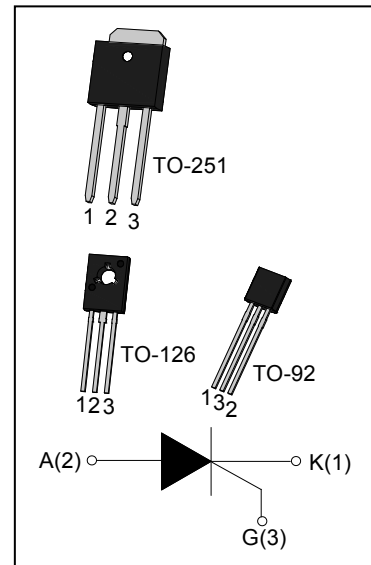
Rev.11.0

DESCRIPTION:

The JX020 SCR series provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on residual current circuit breaker, straight hair, igniter etc. All of the three packages listed above are RoHS compliant. (2011/65/EU)

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	2	A
I_{GT}	≤ 200	μA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range	T_j	-40-125 ^①	$^{\circ}C$
Repetitive peak off-state voltage	V_{DRM}	600	V
Repetitive peak reverse voltage	V_{RRM}	600	V
RMS on-state current	TO-92 ($T_c=95^{\circ}C$)	2	A
	TO-126/ TO-251($T_c=105^{\circ}C$)		
Non repetitive surge peak on-state current ($F=50Hz$ $t_p=10ms$)	I_{TSM}	20	A
Non repetitive surge peak on-state current ($F=60Hz$ $t_p=8.3ms$)	I_{TSM}	22	A
I^2t value for fusing ($t_p=10ms$)	I^2t	2	A^2s
Critical rate of rise of on-state current	di/dt	50	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=125^{\circ}C$)	I_{GM}	0.2	A
Peak gate power ($t_p=20\mu s$, $T_j=125^{\circ}C$)	P_{GM}	0.5	W
Average gate power dissipation($T_j=125^{\circ}C$)	$P_{G(AV)}$	0.1	W

NOTE 1: When we parallel connect a $\leq 1K\Omega$ resistor between Gate and Cathode, the T_j can reach $125^{\circ}C$; if without this resistor, the T_j only can reach $110^{\circ}C$.

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	-	50	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	6	mA
I_H	$I_T=0.05\text{A}$	-	-	5	mA
dV/dt	$V_D=400\text{V } T_j=125^{\circ}\text{C } R_{GK}=1\text{K}\Omega$	60	-	-	V/ μs
	$V_D=400\text{V } T_j=125^{\circ}\text{C } R_{GK}=220\Omega$	500	-	-	
R_d	Dynamic Resistance $T_j=125^{\circ}\text{C}$	-	-	180	$\text{m}\Omega$

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_T=4\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	100	μA

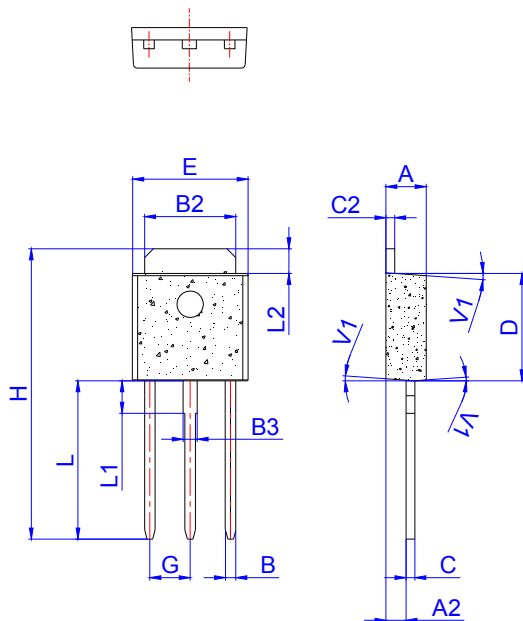
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case	TO-92	10	$^{\circ}\text{C}/\text{W}$
		TO-126	7.0	
		TO-251	6.5	

ORDERING INFORMATION

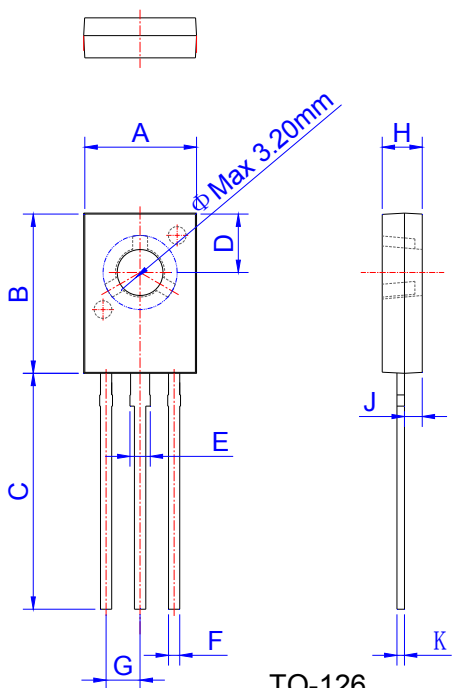
<p>J X 020 U</p> <p>JieJie Microelectronics Co.,Ltd</p> <p>Sensitive gate SCRs</p> <p>$I_{T(RMS)}:2\text{A}$</p>	<p>U:TO-92 H:TO-251 Q:TO-126</p>
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PACKAGE MECHANICAL DATA



TO-251

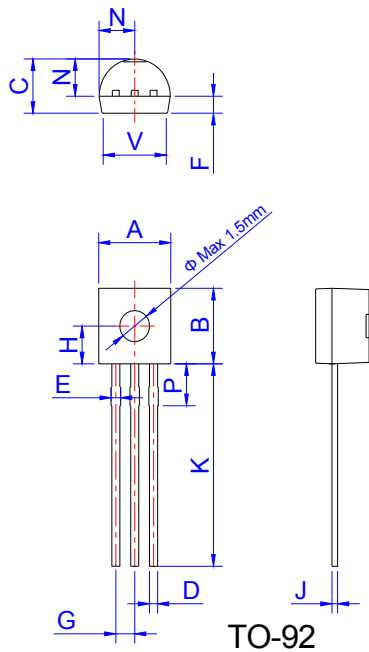
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	



TO-126

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.40		7.80	0.291		0.307
B	10.6		11.2	0.417		0.441
C	15.3		16.3	0.602		0.642
D	3.90		4.10	0.154		0.161
E	1.17		1.47	0.046		0.058
F	0.66		0.86	0.026		0.034
G		2.29			0.090	
H	2.50		2.90	0.098		0.114
J	1.10		1.50	0.043		0.059
K	0.45		0.60	0.018		0.024

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.50		0.70	0.020		0.028
F	-	1.1	-	-	0.043	-
G	-	1.27	-	-	0.050	-
H	-	2.30	-	-	0.091	-
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.86		2.06	0.073		0.081
V	-		4.3	-		0.169

PACKAGE INFORMATION

PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-126	TUBE	50	3,000	18,000
TO-251	TUBE	80	4,000	32,000
PACKAGE	OUTLINE	BAG (PCS)	INNER BOX (PCS)	PER CARTON
TO-92	Shielding Bag	1,000	10,000	30,000

MARKING

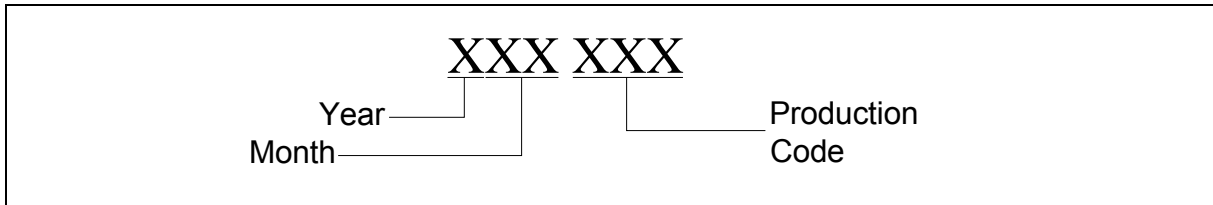
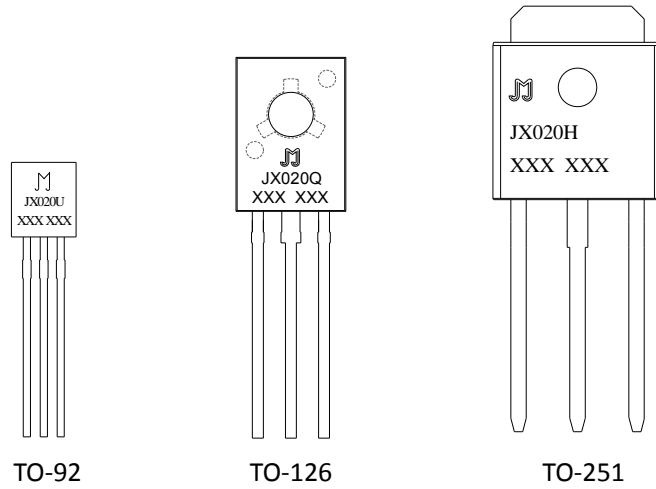


FIG.1: Maximum power dissipation versus RMS on-state current

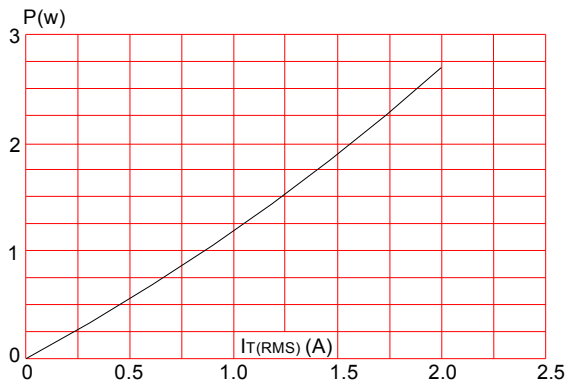


FIG.2: RMS on-state current versus case temperature

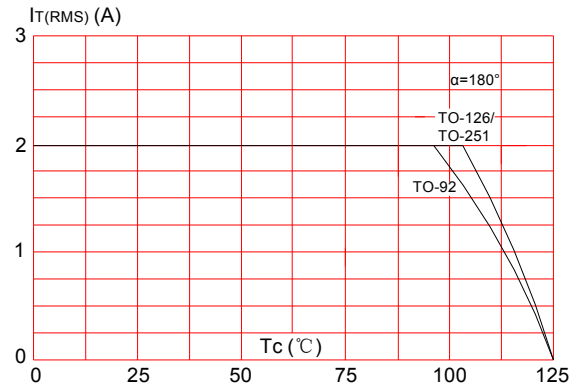


FIG.3: Surge peak on-state current versus number of cycles

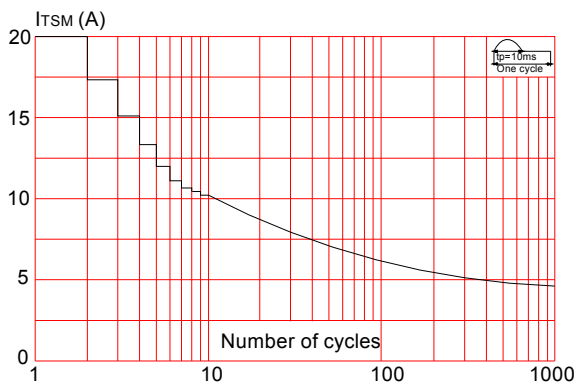


FIG.4: On-state characteristics (maximum values)

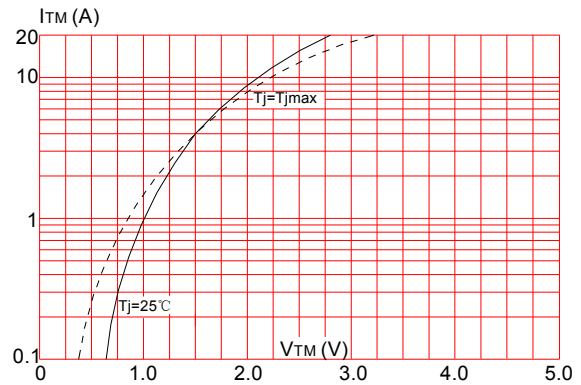


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

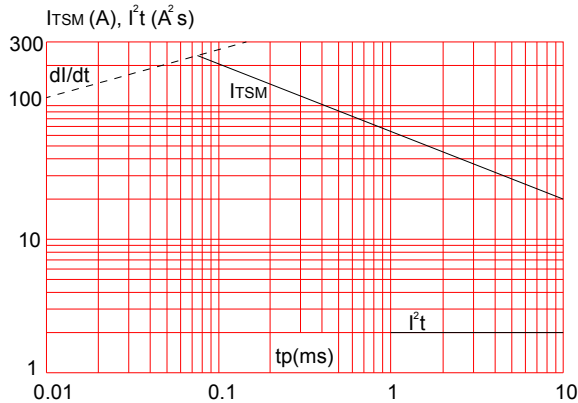
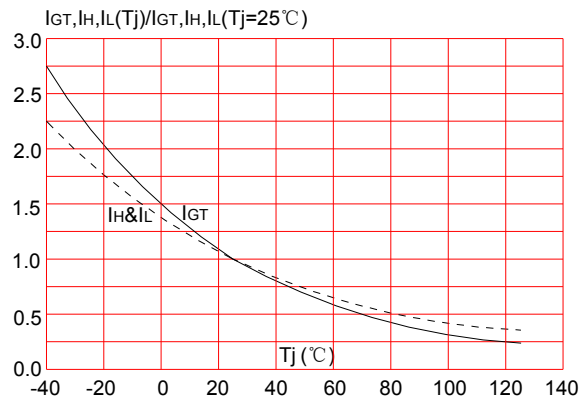



FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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